

# MOS FIELD EFFECT TRANSISTOR **2SJ648**

# P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

#### **DESCRIPTION**

The 2SJ648 is a switching device which can be driven directly by a 2.5 V power source.

The 2SJ648 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

#### **FEATURES**

- 2.5 V drive available
- · Low on-state resistance

RDS(on)1 = 1.45  $\Omega$  MAX. (VGS = -4.5 V, ID = -0.20 A)

RDS(on)2 = 1.55  $\Omega$  MAX. (VGS = -4.0 V, ID = -0.20 A)

RDS(on)3 =  $2.98 \Omega$  MAX. (VGS = -2.5 V, ID = -0.15 A)

## ORDERING INFORMATION

PART NUMBER	PACKAGE			
2SJ648	SC-75 (USM)			

Remark Marking: H1

Remark

## ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Vgs = 0 V)	VDSS	-20	V
Gate to Source Voltage (Vps = 0 V)	Vgss	∓12	V
Drain Current (DC) (T <sub>A</sub> = 25°C)	ID(DC)	∓0.4	Α
Drain Current (pulse) Note1	ID(pulse)	∓1.6	Α
Total Power Dissipation Note2	PT	0.2	W
Channel Temperature	$T_ch$	150	°C
Storage Temperature	Tstg	-55 to +150	°C

**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

# 2. Mounted on ceramic substrate of 300 mm<sup>2</sup> x 0.64 mm.

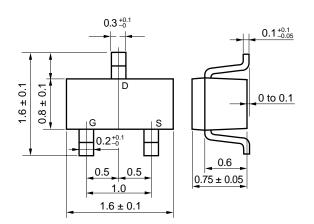
The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

#### Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

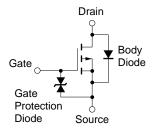
VESD =  $\pm 100$  V TYP. (C = 200 pF, R = 0  $\Omega$ , Single pulse)

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# **PACKAGE DRAWING (Unit: mm)**



# **EQUIVALENT CIRCUIT**



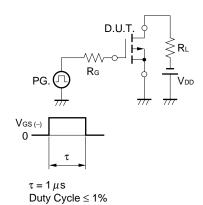


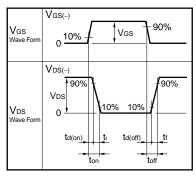
# **ELECTRICAL CHARACTERISTICS (TA = 25°C)**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V <sub>DS</sub> = -20.0 V, V <sub>GS</sub> = 0 V			-1.0	μΑ
Gate Leakage Current	Igss	V <sub>GS</sub> = ∓12 V, V <sub>DS</sub> = 0 V			∓10	μΑ
Gate Cut-off Voltage <sup>Note</sup>	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10.0 V, I <sub>D</sub> = -1.0 mA	-0.8	-1.3	-1.8	V
Forward Transfer Admittance <sup>Note</sup>	y <sub>fs</sub>	V <sub>DS</sub> = -10.0 V, I <sub>D</sub> = -0.20 A	0.2	0.6		S
Drain to Source On-state Resistance Note	R <sub>DS(on)1</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -0.20 A		1.17	1.45	Ω
	R <sub>DS(on)2</sub>	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -0.20 A		1.25	1.55	Ω
	R <sub>DS(on)3</sub>	Vgs = -2.5 V, ID = -0.15 A		2.25	2.98	Ω
Input Capacitance	Ciss	V <sub>DS</sub> = -10.0 V		29		pF
Output Capacitance	Coss	V <sub>GS</sub> = 0 V		15		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		3		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = -10.0 V, I <sub>D</sub> = -0.20 A		23		ns
Rise Time	tr	Vgs = -4.0 V		39		ns
Turn-off Delay Time	td(off)	R <sub>G</sub> = 10 Ω		50		ns
Fall Time	<b>t</b> f			33		ns
Body Diode Forward Voltage	VF(S-D)	IF = 0.40 A, VGS = 0 V		0.93		V

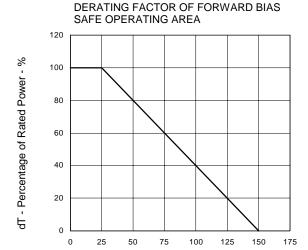
**Note** Pulsed PW $\leq$ 350  $\mu$ s, Duty Cycle $\leq$ 2%

# **TEST CIRCUIT SWITCHING TIME**

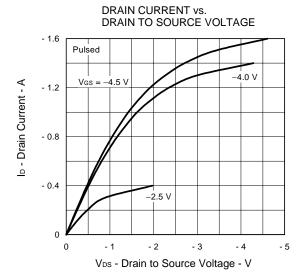




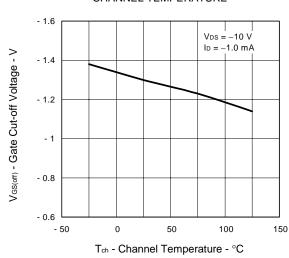
# TYPICAL CHARACTERISTICS (TA = 25°C)



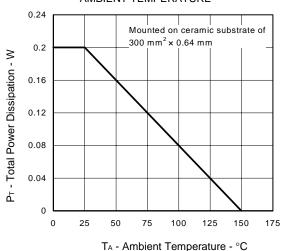
T<sub>A</sub> - Ambient Temperature - °C



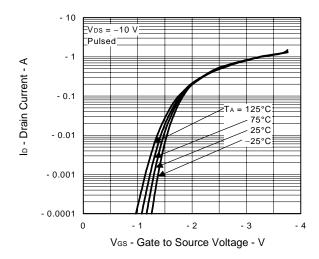
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



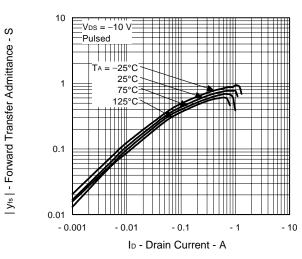
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



FORWARD TRANSFER CHARACTERISTICS



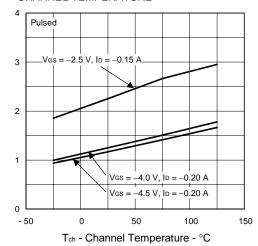
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



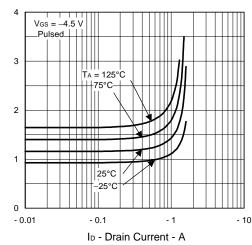
 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - Drain to Source On-state Resistance -  $\Omega$ 

 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  - Drain to Source On-state Resistance -  $\Omega$ 

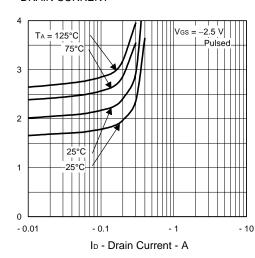
#### DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



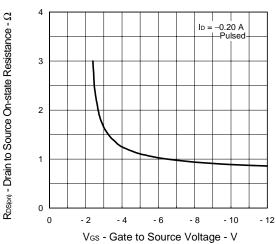
#### DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



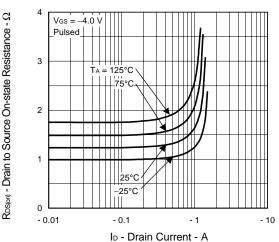
### DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



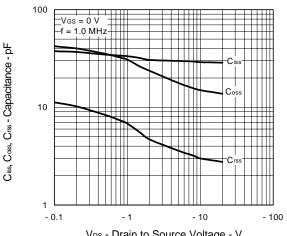
#### DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



#### DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

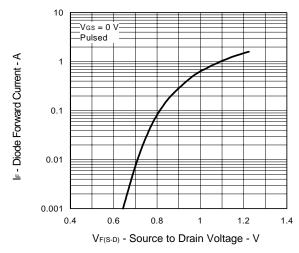


 $\mathsf{Ros}_{(\text{on})}$  - Drain to Source On-state Resistance -  $\Omega$ 

# 

ID - Drain Current - A

## SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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